

DESIGN, FABRICATION AND
CHARACTERIZATION OF CMOS ISFET
FOR pH MEASUREMENTS

CHIN SENG FATT

UNIVERSITI MALAYSIA PERLIS
2009

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**DESIGN, FABRICATION AND
CHARACTERIZATION OF CMOS ISFET
FOR pH MEASUREMENTS**

by

**Chin Seng Fatt
(0630110086)**

A thesis submitted
in fulfillment of the requirements for the degree of
Master of Science (Microelectronic Engineering)

**School of Microelectronic Engineering
UNIVERSITI MALAYSIA PERLIS**

2009

UNIVERSITI MALAYSIA PERLIS

DECLARATION OF THESIS

Author's full name : CHIN SENG FATT
Date of birth : 28 MAY 1982
Title : DESIGN, FABRICATION AND CHARACTERIZATION OF CMOS ISFET
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PROFESSOR DR. UDA BIN HASHIM

Director

Institute of Nano Electronic Engineering
University Malaysia Perlis
(Head Supervisor)

MOHD KHAIRUDDIN BIN MD ARSHAD

Lecturer

School of Microelectronic Engineering
University Malaysia Perlis
(Co-Supervisor)

Check and Approved by

.....
(PROFESSOR DR. UDA BIN HASHIM)

Director / Head Supervisor
Institute of Nano Electronic Engineering
Universiti Malaysia Perlis

(Date:)

School of Microelectronic Engineering
Universiti Malaysia Perlis

2009

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List of Abbreviations

Al	Aluminium
Al ₂ O ₃	Aluminium Oxide
Ag/AgCl	Argentum/ Argentum Chloride (Silver/Silver Chloride)
BSC	Back sided contact
BOE	Buffered Oxide Etch
Ca ²⁺	Calcium ion
ChemFET	Chemically modified field effect transistor
CMOS	Complementary Metal Oxide Semiconductor
CAD	Computer Aided Design
I-V	Current-Voltage
DIW	Deionised Water
DUT	Device Under Test
DC	Direct Current
FET	Field Effect Transistor
FIA	Flow injection analysis
HDL	Hardware Description Language
H ⁺	Hydrogen ion
IGFET	Insulated Gate Field Effect Transistor
ISE	Ion sensitive electrode
ISFET	Ion Sensitive Field Effect Transistor
K ⁺	Kalium ion
Hg	Mercury
Hg ₂ Cl ₂	Mercury Chloride

MIS	Metal Insulator Semiconductor
MOSFET	Metal Oxide Semiconductor Field Effect Transistor
MNOS	Metal-nitride-oxide-semiconductor
MFCL	Micro Fabrication Cleanroom Laboratory
μ TAS	Micro total analysis system
Na^+	Sodium ion
NMOS	N-channel MOSFET
O_2	Oxygen (gas)
PMOS	P-channel MOSFET
PVD	Physical Vapour Deposition
PECVD	Plasma Enhanced Chemical Vapour Deposition
pCO_2	Power of carbon dioxide
pH	Power of hydrogen
PCB	Printed Circuit Board
QC	Quality control
RE	Reference Electrode
rpm	Revolution per minute
SCE	Saturated Calomel Electrode
SCS	Semiconductor Characterization System
SPA	Semiconductor Parameter Analyzer
Si	Silicon
SiO_2	Silicon dioxide or Silicon oxide or Oxide
Si_3N_4	Silicon Nitride
SPICE	Simulation Program With Integrated Circuit Emphasis
SnO_2	Stannum oxide

Ta ₂ O ₅	Tantalum penoxide
TCAD	Technology Computer Aided Design
TAT	Turn around time
VHDL-AMS	Very-High-Speed-Integrated-Circuit Hardware Description Language (VHDL)-Analog and Mixed Signal (AMS)

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List of Symbols

Symbol	Description	Unit
I_D	Drain current	A
V_D	Drain voltage	V
V_G	Gate voltage	V
V_{TH}	Threshold Voltage	V
b	Width of Area	μm
L	Length of Area	μm
μ_n	Electron mobility in a channel	
C_0	Oxide capacitance per unit area	F/m^2
V_{DSAT}	Drain voltage at saturation	V

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List of Publications

- [1] U. Hashim and S. F. Chin, "Simulation of NMOS in Standard CMOS Process using Synopsys' TSUPREM-4 and MEDICI," in *Malaysian Technical Universities Conference on Engineering and Technology (MUCET)*, Universiti Teknologi Tun Hussein Onn, 2006, pp. 36-39.
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- [9] U. Hashim, S. F. Chin, and S. Sakrani, "Application of Synopsys' Taurus TCAD in Developing CMOS Fabrication Process Modules," *International Journal of Nanoelectronics and Materials*, vol. 2, pp. 1-10, 2009.

List of Awards

1. Research and Innovation Awards 2009 **Gold** Medalist
2. BioInno Awards 2009 **Silver** Medalist
3. PECIPTA 2009 **Silver** Medalist
4. Malaysia Invention and Innovation Awards 2009 **Silver** Medalist
5. BioInno Awards 2008 **Bronze** Medalist
6. Research and Innovation Awards 2008 **Bronze** Medalist

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